

ABSTRACT

A method of forming a self-aligned contact hole suitable for a semiconductor substrate having a pair of gate electrodes. First, a nitride etching stop layer is formed over the gate electrodes and the semiconductor substrate. Then, an oxide
5 insulating layer is formed on the nitride etching stop layer, Next, the oxide insulating layer is plasma-etched by an etching gas containing C_5F_8 and CHF_3 or C_4F_6 and CHF_3 so as to form a self-aligned contact hole between the pair of gate electrode.